

Amendments to the Claims

Claims 1-40 (Cancelled).

41. (Previously presented) A transistor structure, comprising:
a gate oxide layer on a semiconductive substrate, the gate oxide layer comprising silicon dioxide and having a total thickness of about 5Å; the gate oxide layer having a nitrogen-enriched region which is only in an upper half of the gate oxide layer;
a conductive layer on the gate oxide layer; and
source/drain regions within the semiconductive substrate; the source/drain regions being gatedly connected to one another by the conductive layer.

42. (Original) The structure of claim 41 wherein the conductive layer comprises conductively-doped silicon.

43. (Original) The structure of claim 41 wherein the conductive layer comprises p-type conductively-doped silicon.

Claims 44-47 (Cancelled).

48. (Withdrawn) A transistor structure comprising:
a gate oxide region disposed directly on a semiconductive substrate and having an upper surface, the gate oxide region having a thickness of 5\AA , an upper half of the gate oxide region being nitrogen-enriched relative to a lower half; and
a conductive layer in physical contact with the upper surface of the gate oxide region.
49. (Withdrawn) The transistor structure of claim 48 wherein the gate oxide region comprises silicon dioxide.
50. (Withdrawn) The transistor structure of claim 48 wherein the gate oxide region comprises borophosphosilicate glass.
51. (Withdrawn) The transistor structure of claim 48 wherein the conductive layer is a first conductive layer, and further comprising a second conductive layer over the first conductive layer.
52. (Withdrawn) The transistor structure of claim 51 wherein the first conductive layer comprises conductively doped silicon and wherein the second conductive layer comprises a metal silicide.